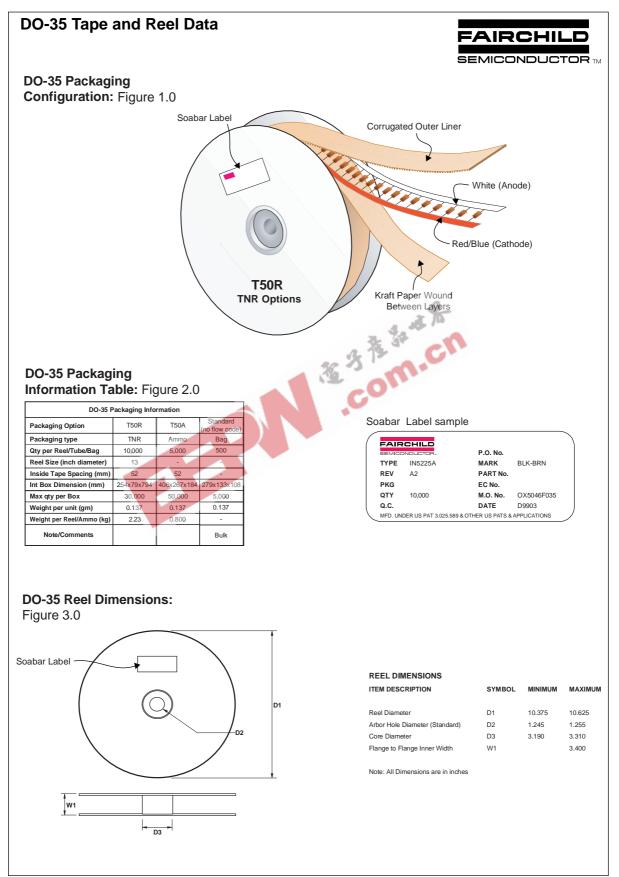
	NDUCTOR TM		
	FDH/FDLL 30	00/A / 333	
l	DO-35	FDLL300 BROWN FDLL300A BROWN FDLL333 BROWN	RKING 2ND BAND GREEN YELLOW BLUE
Hiah	Conductance Low Leakage	Diada	
Sourced fr	rom Process 1M. See MMBD1501/A-1505/A for cha ute Maximum Ratings* TA = 25°C un	aracteristics.	
Sourced fr Absolu ymbol	rom Process 1M. See MMBD1501/A-1505/A for cha ute Maximum Ratings* TA = 25°C un Parameter	eracteristics. less otherwise noted Value	Units
Sourced fr Absolu ymbol	rom Process 1M. See MMBD1501/A-1505/A for cha ute Maximum Ratings* TA = 25°C un Parameter Working Inverse Voltage	aracteristics. less otherwise noted Value 125	V
Sourced fr Absolu ymbol	rom Process 1M. See MMBD1501/A-1505/A for cha ute Maximum Ratings* TA = 25°C un Parameter Working Inverse Voltage Average Rectified Current	aracteristics. less otherwise noted Value 125 200	V mA
Sourced fr Absolu ymbol	rom Process 1M. See MMBD1501/A-1505/A for cha ute Maximum Ratings* TA = 25°C un Parameter Working Inverse Voltage Average Rectified Current DC Forward Current	aracteristics. less otherwise noted Value 125 200 500	V mA mA
Sourced fi Absolu ymbol	rom Process 1M. See MMBD1501/A-1505/A for cha ute Maximum Ratings* TA = 25°C un Parameter Working Inverse Voltage Average Rectified Current DC Forward Current Recurrent Peak Forward Current	aracteristics. less otherwise noted Value 125 200	V mA
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Sourced fr Absolu ymbol w	rom Process 1M. See MMBD1501/A-1505/A for cha Ute Maximum Ratings* TA = 25°C un Parameter Working Inverse Voltage Average Rectified Current DC Forward Current Recurrent Peak Forward Current Peak Forward Surge Current Pulse width = 1.0 second Pulse width = 1.0 microsecond	aracteristics. less otherwise noted Value 125 200 500 600 1.0 4.0	V mA mA MA A A
Sourced fr Absolu Symbol	rom Process 1M. See MMBD1501/A-1505/A for cha Ute Maximum Ratings* TA = 25°C un Parameter Working Inverse Voltage Average Rectified Current DC Forward Current Recurrent Peak Forward Current Peak Forward Surge Current Pulse width = 1.0 second Pulse width = 1.0 microsecond Storage Temperature Range	Value 125 200 500 600 1.0 4.0 -65 to +200	V mA mA MA A A A C
Sourced fr Absolu Symbol (IV surge)	rom Process 1M. See MMBD1501/A-1505/A for cha Ute Maximum Ratings* TA = 25°C un Parameter Working Inverse Voltage Average Rectified Current DC Forward Current Recurrent Peak Forward Current Peak Forward Surge Current Pulse width = 1.0 second Pulse width = 1.0 microsecond Storage Temperature Range Operating Junction Temperature	Value 125 200 500 600 1.0 4.0 -65 to +200 175	V mA mA MA A A
Sourced fr Absolu Symbol V _{IV} (surge) stg J *These rating NOTES: 1) These ratin 2) These are	rom Process 1M. See MMBD1501/A-1505/A for cha Ute Maximum Ratings* TA = 25°C un Parameter Working Inverse Voltage Average Rectified Current DC Forward Current Recurrent Peak Forward Current Peak Forward Surge Current Pulse width = 1.0 second Pulse width = 1.0 microsecond Storage Temperature Range	eracteristics.	V mA mA MA A A A C
Sourced fr Absolu Symbol VIV Surge) stg J *These rating NOTES: 1) These rating 2) These rating These rating	rom Process 1M. See MMBD1501/A-1505/A for cha Ite Maximum Ratings* TA = 25°C un Parameter Working Inverse Voltage Average Rectified Current DC Forward Current Recurrent Peak Forward Current Peak Forward Surge Current Pulse width = 1.0 second Pulse width = 1.0 microsecond Storage Temperature Range Operating Junction Temperature gs are lainting values above which the serviceability of any semicond steady state limits. The factory should be consulted on applications in	eracteristics.	V mA mA MA A A C °C °C
Sourced fr Absolu Symbol V _{IV} (surge) *These rating NOTES: 1) These ratin 2) These ratin	rom Process 1M. See MMBD1501/A-1505/A for cha Ite Maximum Ratings* TA = 25°C un Parameter Working Inverse Voltage Average Rectified Current DC Forward Current Recurrent Peak Forward Current Peak Forward Surge Current Pulse width = 1.0 second Pulse width = 1.0 microsecond Storage Temperature Range Operating Junction Temperature gs are limiting values above which the serviceability of any semicond ings are based on a maximum junction temperature of 200 degrees C steady state limits. The factory should be consulted on applications in al Characteristics TA = 25°C unless other	Aracteristics. Less otherwise noted	V mA mA MA A A A C
Sourced fr Absolu Symbol /IV surge) stg J *These rating NOTES: 1) These rating 2) These rating Therm Symbol	rom Process 1M. See MMBD1501/A-1505/A for characteristics TA = 25°C un Parameter Working Inverse Voltage Average Rectified Current DC Forward Current DC Forward Current Peak Forward Surge Current Pulse width = 1.0 second Pulse width = 1.0 second Pulse width = 1.0 microsecond Storage Temperature Range Operating Junction Temperature gs are lainting values above which the serviceability of any semicond instance and a maximum junction temperature of 200 degrees C steady state limits. The factory should be consulted on applications in al Characteristics TA = 25°C unless othe Characteristic	eracteristics. less otherwise noted Value 125 200 500 600 1.0 4.0 -65 to +200 175 uctor device may be impaired. .: involving pulsed or low duty cycle operations. rwise noted Max FDH/FDLL 300/A / 333	V mA mA MA A A C °C °C
Sourced fr Absolu Symbol V _{IV} 0 (surge) stg J *These rating NOTES: 1) These ratin 2) These are	rom Process 1M. See MMBD1501/A-1505/A for cha Ite Maximum Ratings* TA = 25°C un Parameter Working Inverse Voltage Average Rectified Current DC Forward Current Recurrent Peak Forward Current Peak Forward Surge Current Pulse width = 1.0 second Pulse width = 1.0 microsecond Storage Temperature Range Operating Junction Temperature gs are limiting values above which the serviceability of any semicond ings are based on a maximum junction temperature of 200 degrees C steady state limits. The factory should be consulted on applications in al Characteristics TA = 25°C unless other	Aracteristics. Less otherwise noted	V mA mA MA A A °C °C °C

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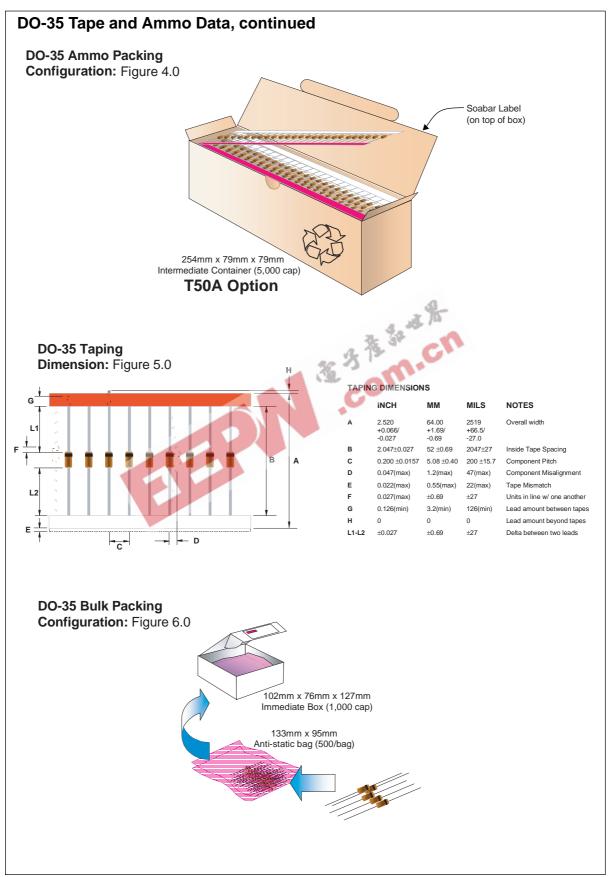
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Symbol	Para	meter	Test Conditions	Min	Max	Units
Bv	Breakdown Voltage	e	I _R = 100 μA	150		V
I _R	Reverse Current	FDH/FDLL 300/A	V _R = 125 V		1.0	nA
			$V_{R} = 125 V, T_{A} = 150^{\circ}C$		3.0	μA
		FDH/FDLL 333	$V_{R} = 125 V$		3.0	nA
	Famural Valtana		$V_{\rm R} = 125 \text{ V}, \text{T}_{\rm A} = 100^{\circ}\text{C}$		500	nA
V _F	Forward Voltage	FDH/FDLL 300/A FDH/FDLL 300	I _F = 1.0 mA I _F = 5.0 mA		680 750	mV mV
		FDH/FDLL 300A	$I_F = 5.0 \text{ mA}$ $I_F = 5.0 \text{ mA}$		760	mV
		FDH/FDLL 300/A	$I_{\rm F} = 10 {\rm mA}$		800	mV
		FDH/FDLL 300	$I_F = 50 \text{ mA}$		880	mV
		FDH/FDLL 300A	$I_{\rm F} = 50 \rm mA$		890	mV
		FDH/FDLL 300/A	$I_{\rm F} = 100 {\rm mA}$		920	mV
		FDH/FDLL 300/A	I _F = 200 mA		1.0	V
		FDH/FDLL 333	I _F = 50 mA	800	890	mV
			I _F = 100 mA	830	940	mV
			I _F = 150 mA	860	970	mV
			I _F = 200 mA	0.87	1.05	V
			I _F = 250 mA	0.88	1.08	V
0	Diada Caracitara		$I_F = 300 \text{ mA}$	0.9	1.15	V v
Co	Diode Capacitance	9	V _R = 0, f = 1.0 MHz		6.0	pF

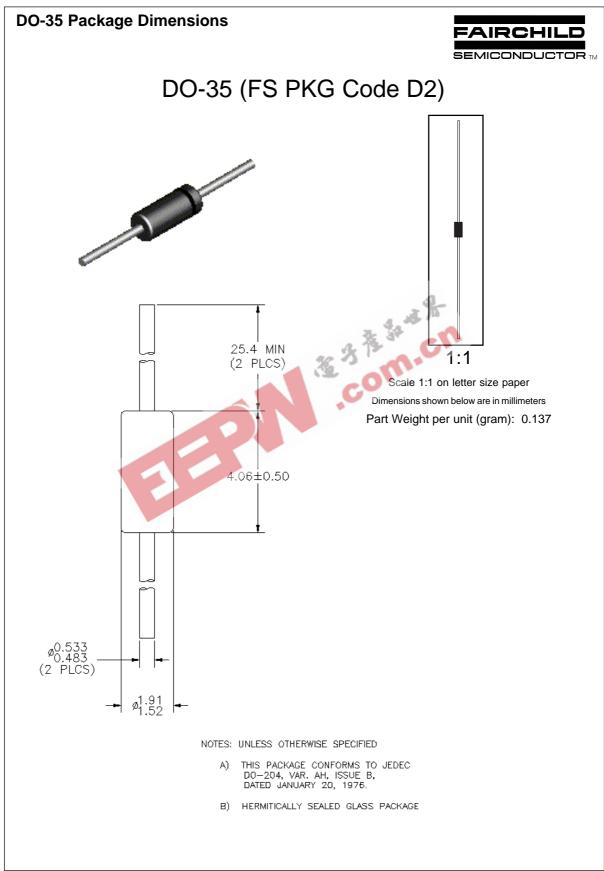
FDH300/A / FDLL300/A / FDH333 / FDLL333

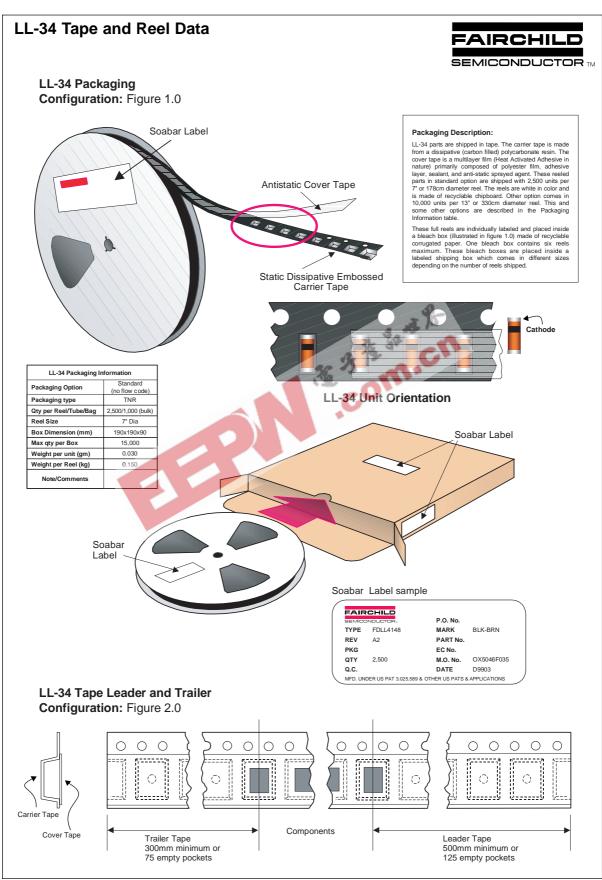


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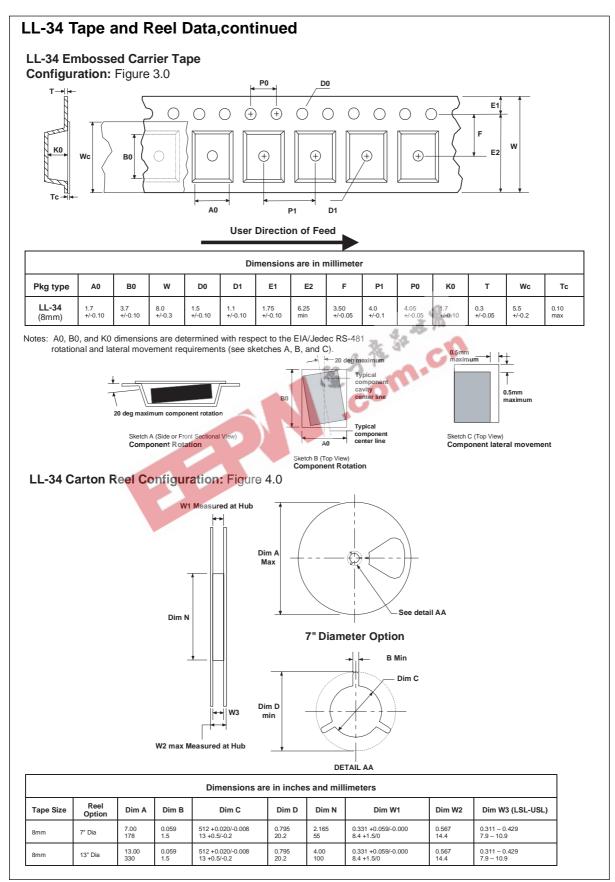
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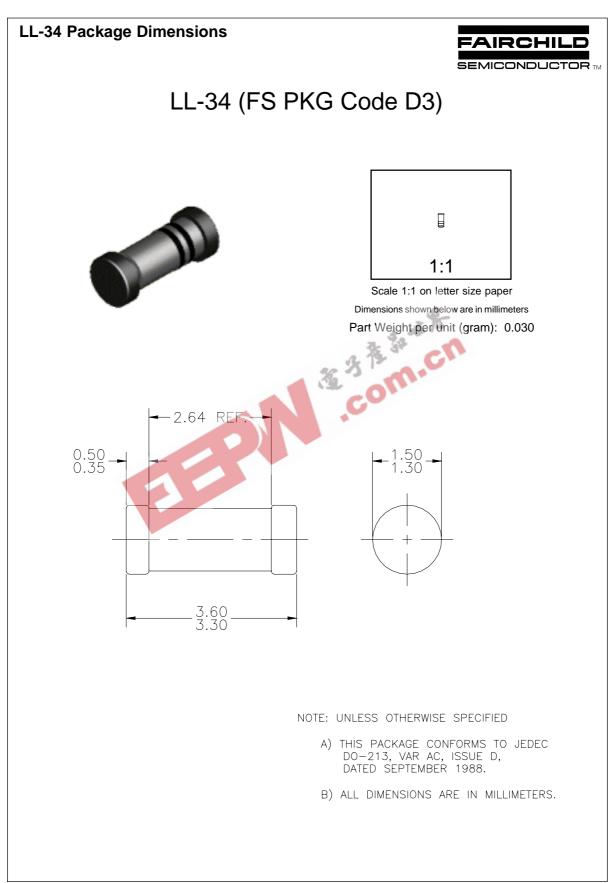


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Definition of Terms

Datasheet Identification	Product Status	Definition
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